

# RELIABILITY MONITOR

PRODUCT	MONITOR DATE	DATE CODE	ASSEMBLY FACILITY	ASSEMBLY LOT NO	PROCESS TYPE	PACKAGE TYPE
DS2175	Jan-97	9643 D1	ANAM, K.	DN634667AAA1	2.0μ OXIDE	16 SOIC

**STRESS/JOB NO.**

**READPOINT  
(Sample Size/No. of Fails)**

Preconditioning (P/C):  
T/C: -55°C to +125°C, 10~  
HTC Vapor Phase, P-18897

<u>Electrical</u>	<u>Cum %</u>
233/0	0.0%

Sonoscan  
P-18948

<u>Post Vapor Phase</u>
4/0

Infant / High Voltage Life  
125°C, 7.0 V.  
P-18949, P-19012

<u>48 Hr</u>	<u>336 Hr</u>	<u>1KHr</u>	<u>*Failure Rate</u>
228/0	77/0	77/0	30 Fits

\*Chi Squared Method, 60% C. L., 55°C & 5.5V; Temperature Derating: Ea = 0.7 ev; Voltage Derating B = 1.0

Temp Cycle  
-55°C to +125°C  
P-19013

<u>300 ~</u>	<u>1K ~</u>	<u>Cum %</u>
36/0	36/0	0.0%

Biased Moisture  
85°C/85% RH, 5.5 V.  
P-19014

<u>274 Hr</u>	<u>959 Hr</u>	<u>Cum %</u>
77/0		

Autoclave  
121°C/100% RH, 2 Atmos  
P-19015

<u>96 Hr</u>	<u>Cum %</u>
38/0	0.0%

**Failure Mode**

**Failure Analysis**